

IN THE CLAIMS:

Please cancel Claims 1 to 6 without prejudice or disclaimer of subject matter. Please amend Claims 7 and 8 as shown below.

1. to 6. (Cancelled)

7. (Currently Amended) A semiconductor substrate comprising:

a substrate of silicon having purity of less than 99.99%; and

a surface layer composed of silicon provided on the substrate of silicon, the surface layer containing an inclined plane and plural grooves of each formed by a gap portion communicated with the inclined plane in a surface layer composed of silicon.

8. (Currently Amended) A semiconductor substrate comprising:

a substrate of silicon having purity of less than 99.99%; and

a surface layer composed of silicon provided on the substrate of silicon, the surface layer containing a surface portion having an inclined plane affected by a crystal structure of silicon and plural protrusions that each having an overhang in a lateral direction in a surface layer composed of silicon,

wherein plural grooves each having openings an opening narrowed due to
by the protrusions overhanging in the lateral direction overhang of at least one of the
protrusions are formed in the surface ~~portion~~ layer.

9. (Original) The semiconductor substrate according to claim 8, wherein the inclined plane is (111) surface or (100) surface of a silicon crystal.

10. (Original) The semiconductor substrate according to claim 8, wherein a width of the opening of each groove is 0.1 to 50 μm .

11. (Original) The semiconductor substrate according to claim 8, wherein a vertical depth from the opening of each groove to a deepest end of each groove is 5 to 100 μm .

12. (Original) A solar cell comprising the semiconductor substrate according to claim 8 as a component,
wherein a P-N junction is formed on the surface layer composed of silicon.

13. (Original) A solar cell comprising a collector electrode crossing over the plural grooves on the semiconductor substrate according to claim 8.